



YJQ018G10AHQ

N-Channel Enhancement Mode Field Effect Transistor

Product Summary

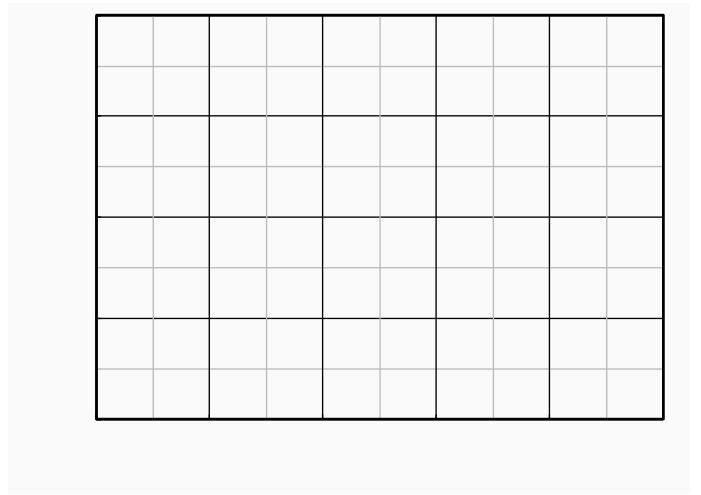
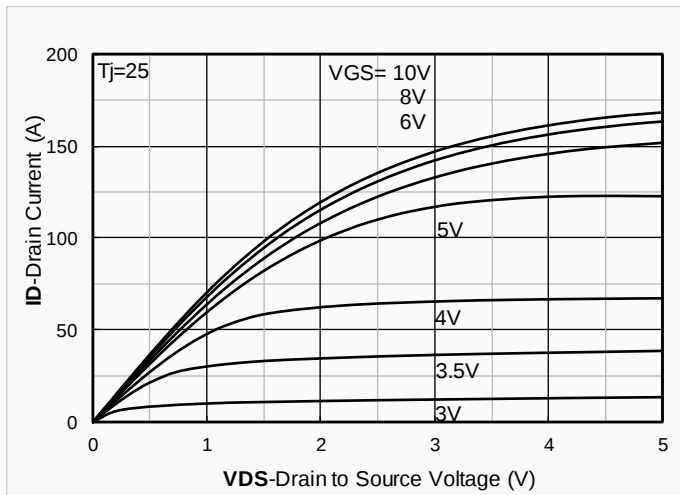
- V_{DS} 100V
- I_D 40A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) 18m Ω
- $R_{DS(ON)}$ (at $V_{GS}=4.5V$) 22.5m Ω
- 100% EAS Tested
- 100% V_{DS} Tested

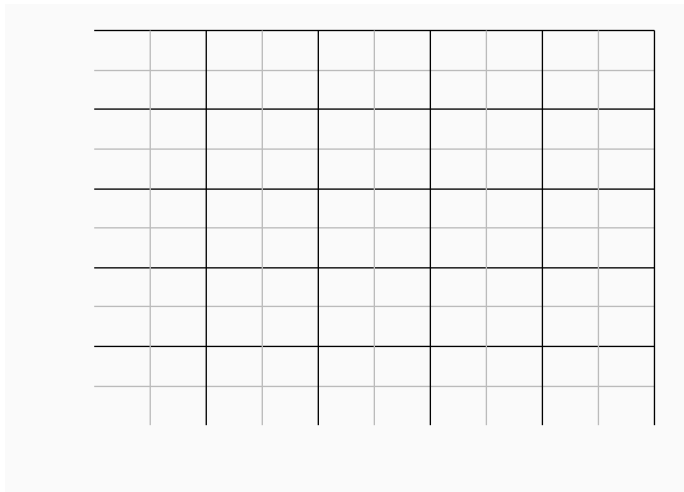
General Description

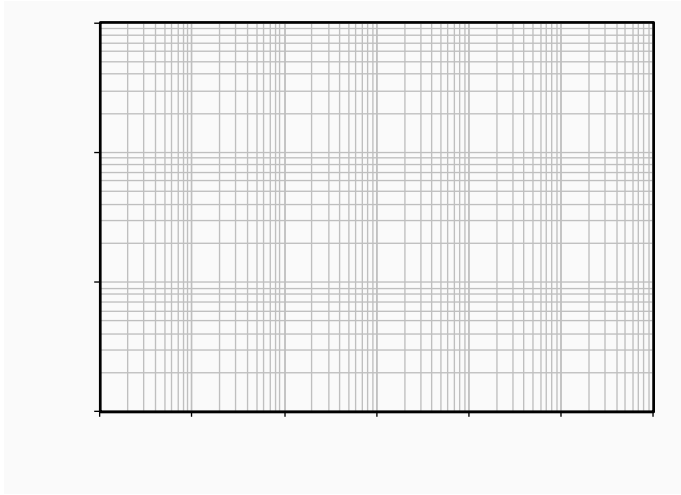
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating

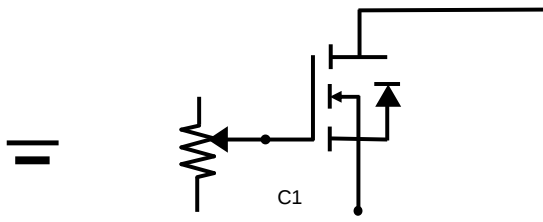


■Typical Electrical and Thermal Characteristics Diagrams



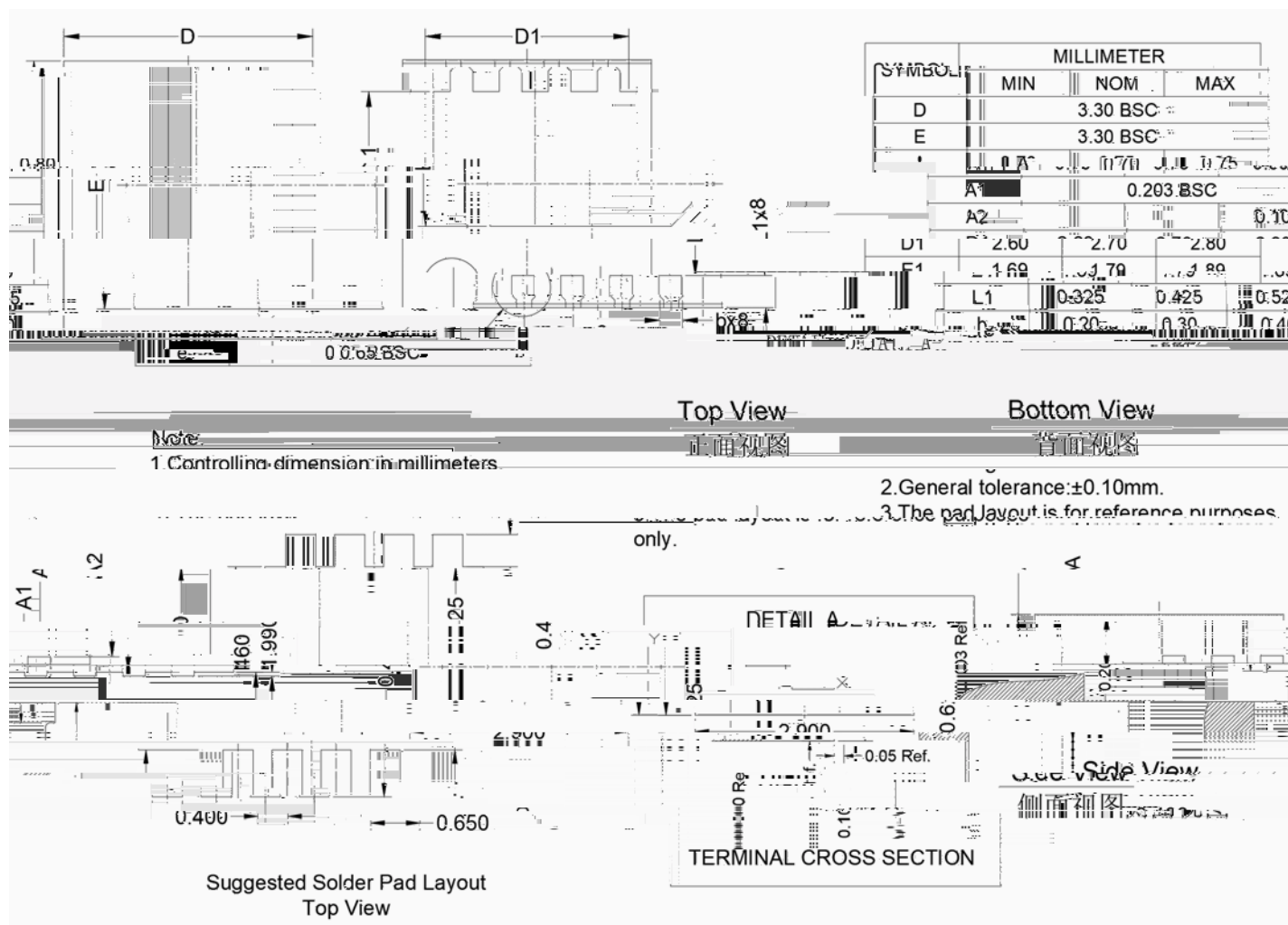








■ DFN3333-8L-WF Package information





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